Catalog # 93-4932 Indium(III) chloride, anhydrous (99.999%-In) PURATREM

Thermal Behavior:

- Melting point: 586°C [1]
- Boiling point: 800°C
- Sublimation: ~387°C/0.76 Torr [2]
- Vapor pressure studies available in [1, 3]

Technical Notes:

1. ALD/CVD precursor and dopant for indium thin film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
In_2O_3	ALD ALD	275°C 275°C	- 7.5 Torr	H_2O_2 H_2O	500°C 500°C	4 5
$Zr:In_2O_3$	ALD	275°C	7.5 Torr	$ZrCl_4$	500°C	6
In_2Se_3	ALD ALD	285°C 110°C	7.5 Torr -	$(R_3Si)_2Se$ H_2Se	295°C 310-380°C	7 8
$CuIn_xS_y$	ALD	300-345°C	1.5 Torr	CuCl, H_2S	350-500°C	9-10

References:

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4. *Electrochem. Solid-State Lett.* **1998**, *1*, 156.
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8. *Electronics* **2017**, *6*, 27.
9. *Thin Solid Films*, **2003**, *431*, 492.
10. *Chem. Vap. Deposition*, **2004**, *10*, 45.